

Jonathan Pelz

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/436024/publications.pdf>

Version: 2024-02-01

19
papers

362
citations

1040056

9
h-index

1058476

14
g-index

19
all docs

19
docs citations

19
times ranked

375
citing authors

#	ARTICLE	IF	CITATIONS
1	Spatially-resolved spectroscopic measurements of $i>Ec</i>$ ~ 0.57 eV traps in AlGaIn/GaN high electron mobility transistors. Applied Physics Letters, 2013, 102, .	3.3	91
2	Evolution of atomic-scale roughening on Si(001) (2×1) surfaces resulting from high temperature oxidation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1995, 13, 772-776.	2.1	54
3	Ballistic-electron emission microscopy studies of charge trapping in SiO ₂ . Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2864.	1.6	42
4	Elevated temperature oxidation and etching of the Si(111) 7×7 surface observed with scanning tunneling microscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 1649-1653.	2.1	41
5	Direct nm-Scale Spatial Mapping of Traps in CIGS. IEEE Journal of Photovoltaics, 2015, 5, 1482-1486.	2.5	32
6	Nm-scale measurements of fast surface potential transients in an AlGaIn/GaN high electron mobility transistor. Applied Physics Letters, 2012, 100, .	3.3	31
7	Nanometer-scale investigation of metal-SiC interfaces using ballistic electron emission microscopy. Journal of Electronic Materials, 1998, 27, 345-352.	2.2	19
8	Correlation of electrical spin injection and non-linear charge-transport in Fe/MgO/Si. Applied Physics Letters, 2013, 103, .	3.3	17
9	Spatial correlation of the EC-0.57 eV trap state with edge dislocations in epitaxial n-type gallium nitride. Journal of Applied Physics, 2018, 123, .	2.5	11
10	Investigation of ultrathin SiO ₂ film thickness variations by ballistic electron emission microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2302.	1.6	9
11	Calculated potential profile near charged threading dislocations at metal/semiconductor interfaces. Journal of Applied Physics, 2002, 92, 6010-6013.	2.5	6
12	Relaxed InAsP layers grown on step graded InAsP buffers by solid source MBE. Materials Research Society Symposia Proceedings, 2002, 722, 1021.	0.1	4
13	OBSERVATION OF DIRECT-CURRENT-INDUCED STEP BENDING PATTERNS ON Si(001). Surface Review and Letters, 2000, 07, 577-582.	1.1	3
14	Local trap spectroscopy on cross-sectioned AlGaIn/GaN devices with $i>in situ</i>$ biasing. Applied Physics Letters, 2019, 114, .	3.3	2
15	Alignment of Adsorbate-Induced Defects on Silicon(001) 2×1 Observed with STM. Materials Research Society Symposia Proceedings, 1993, 318, 25.	0.1	0
16	Ultrahigh vacuum dual fluid line rotatable connector. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 674-675.	2.1	0
17	Nanoscale Characterization of Metal/Semiconductor Nanocontacts. AIP Conference Proceedings, 2005, , .	0.4	0
18	Direct nm-scale spatial mapping of traps in CIGS. , 2015, , .		0

#	ARTICLE	IF	CITATIONS
19	Correlative Defect Characterization in Semiconductors via Electron Channeling Contrast Imaging and Scanning Deep Level Transient Spectroscopy. <i>Microscopy and Microanalysis</i> , 2018, 24, 1056-1057.	0.4	0